

FERROELECTRIC MEMORY STRUCTURE AND FABRICATION METHOD THEREOF

ABSTRACT OF THE DISCLOSURE

A ferroelectric memory structure is disclosed. The ferroelectric memory structure includes a substrate, an insulating layer formed on the substrate, a plurality of oxide electrodes formed on the insulating layer, a ferroelectric layer formed on the insulating layer and the plurality of oxide electrodes, and a plurality of metallic electrodes formed on the ferroelectric layer and corresponding to the plurality of the oxide electrodes.